

# MSARS200S20LP

## MSARS200S20LRP

### Features

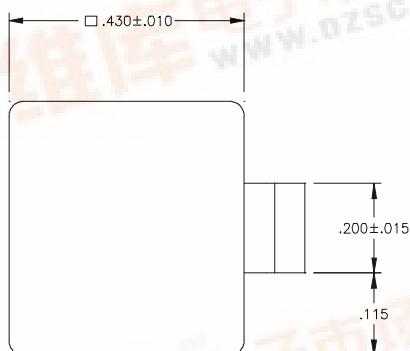
- passivated mesa structure for very low leakage currents
- Epitaxial structure minimizes forward voltage drop
- Low profile plastic surface mount package with CTE matched base
- Low package inductance
- Very low thermal resistance
- Available as standard polarity (strap-to-anode, MSARS200S20LP) and reverse polarity (strap-to-cathode: MSARS200S20LRP)

**200 Volts  
200 Amps**

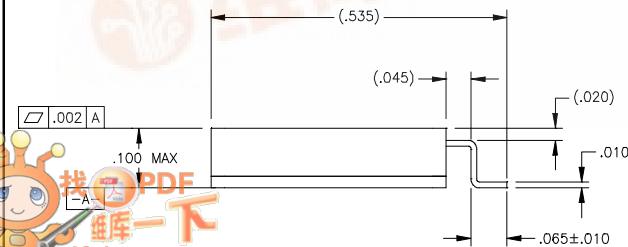
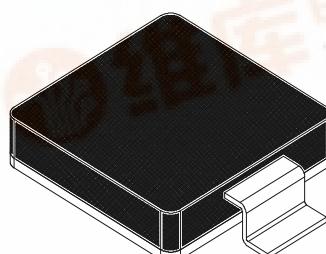
**HIGH CURRENT  
CAPABILITY &  
LOW VOLTAGE  
DROP STANDARD  
RECOVERY  
RECTIFIER**

### Maximum Ratings @ 25°C (unless otherwise specified)

DESCRIPTION	SYMBOL	MAX.	UNIT
Peak Repetitive Reverse Voltage	$V_{RRM}$	200	Volts
Working Peak Reverse Voltage	$V_{RWM}$	200	Volts
DC Blocking Voltage	$V_R$	200	Volts
Average Rectified Forward Current, $T_c \leq 125^\circ\text{C}$	$I_{F(\text{ave})}$	200	Amps
derating, forward current, $T_c \geq 125^\circ\text{C}$	$dI_F/dT$	4	Amps/ $^\circ\text{C}$
Nonrepetitive Peak Surge Current, $t_p = 8.3 \text{ ms}$ , half-sinewave	$I_{FSM}$	750	Amps
Junction Temperature Range	$T_j$	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +125	$^\circ\text{C}$
Thermal Resistance, Junction to Case:	$\theta_{JC}$	0.20	$^\circ\text{C}/\text{W}$



**Mechanical Outline**  
**Plastic ThinKey™3**



Molybdenum pad with Ni plating and Sn63 solder finish

Cu/Invar/Cu strap with Ni plating and Sn63 solder finish on foot

# MSARS200S20LP

# MSARS200S20LRP

## Electrical Parameters

DESCRIPTION	SYMBOL	CONDITIONS	MIN	TYP.	MAX	UNIT
Reverse (Leakage) Current	IR <sub>25</sub>	VR= 200 Vdc, Tc= 25°C	-	1	50	µA
	IR <sub>100</sub>	VR= 200 Vdc, Tc= 100°C	-	10	-	µA
	IR <sub>125</sub>	VR= 200 Vdc, Tc= 125°C	-	25	1000	µA
Forward Voltage pulse test, pw= 300 µs d/c≤ 2%	VF <sub>a25</sub>	IF= 10 mA, Tc= 25°C		570	-	mV
	VF <sub>b25</sub>	IF= 100 mA, Tc= 25°C		640	-	mV
	VF <sub>c25</sub>	IF= 500 mA, Tc= 25°C		700	-	mV
	VF <sub>a125</sub>	IF= 10 mA, Tc= 125°C		375	-	mV
	VF <sub>b125</sub>	IF= 100 mA, Tc= 125°C		470	-	mV
	VF <sub>c125</sub>	IF= 500 mA, Tc= 125°C		540	-	mV
	VF <sub>a-55</sub>	IF= 10 mA, Tc= -55°C		710	-	mV
	VF <sub>b-55</sub>	IF= 100 mA, Tc= -55°C		770	-	mV
	VF <sub>c-55</sub>	IF= 500 mA, Tc= -55°C		810	-	mV
	VF1	IF= 5 A, Tc= 25°C		780	830	mV
	VF2	IF= 10 A, Tc= 25°C		810	-	mV
	VF3	IF= 25 A, Tc= 25°C		845	900	mV
	VF4	IF= 50 A, Tc= 25°C		875	940	mV
	VF5	IF= 100 A, Tc= 25°C		905	975	mV
	VF6	IF= 150 A, Tc= 25°C		1010	-	mV
	VF7	IF= 200 A, Tc= 25°C		1100	-	mV
	VF8	IF= 250 A, Tc= 25°C		1165	-	mV
	VF9	IF= 300 A, Tc= 25°C		1250	-	mV
	VF10	IF= 5 A, Tc= -55°C		880	930	mV
	VF11	IF= 10 A, Tc= -55°C		900	-	mV
	VF12	IF= 25 A, Tc= -55°C		930	990	mV
	VF13	IF= 50 A, Tc= -55°C		955	1030	mV
	VF14	IF= 100 A, Tc= -55°C		985	1070	mV
	VF15	IF= 5 A, Tc= 125°C		640	690	mV
	VF16	IF= 10 A, Tc= 125°C		670	-	mV
	VF17	IF= 25 A, Tc= 125°C		715	775	mV
	VF18	IF= 50 A, Tc= 125°C		750	825	mV
	VF19	IF= 100 A, Tc= 125°C		790	865	mV
Junction Capacitance	C <sub>j1</sub>	VR= 10 Vdc		1500	2250	pF
Breakdown Voltage	BVR	IR= 500 µA, Tc= 25°C	200	205	n/a	V
Reverse Recovery Time	trr	IF= .5 A, IR= 1 A, IRR=.25 A		1.5	5	µs